List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/2457729/publications.pdf Version: 2024-02-01

214 papers	1,819 citations	361296 20 h-index	395590 33 g-index
215	215	215	1990
all docs	docs citations	times ranked	citing authors

DETED I VTVVN

#	Article	IF	CITATIONS
1	Zinc oxide - analogue of GaN with new perspective possibilities. Crystal Research and Technology, 2004, 39, 980-992.	0.6	142
2	Low-Temperature Reduction of Graphene Oxide: Electrical Conductance and Scanning Kelvin Probe Force Microscopy. Nanoscale Research Letters, 2018, 13, 139.	3.1	63
3	Raman Submicron Spatial Mapping of Individual Mn-doped ZnO Nanorods. Nanoscale Research Letters, 2017, 12, 351.	3.1	51
4	The role of beneficial bacteria wall elasticity in regulating innate immune response. EPMA Journal, 2015, 6, 13.	3.3	48
5	Real-time atomic force microscopy imaging of photoinduced surface deformation in AsxSe100â ^{~°} x chalcogenide films. Applied Physics Letters, 2010, 96, 111908.	1.5	45
6	Microscopic and optical investigation of Ge nanoislands on silicon substrates. Nanotechnology, 2002, 13, 81-85.	1.3	44
7	DNA nanotechnology of carbon nanotube cells: physico-chemical models of self-organization and properties. Materials Science and Engineering C, 2002, 19, 41-45.	3.8	43
8	Photoinduced mass-transport based holographic recording of surface relief gratings in amorphous selenium films. Applied Physics Letters, 2011, 99, 051906.	1.5	39
9	Electrolytic molybdenum oxides in lithium batteries. Journal of Solid State Electrochemistry, 2005, 9, 96-105.	1.2	38
10	Substrate effects on the strain relaxation in GaN/AlN short-period superlattices. Nanoscale Research Letters, 2012, 7, 289.	3.1	37
11	Surface morphology of as-deposited and illuminated As–Se chalcogenide thin films. Journal of Non-Crystalline Solids, 2009, 355, 1993-1997.	1.5	36
12	Vickers Hardness of Diamond and cBN Single Crystals: AFM Approach. Crystals, 2017, 7, 369.	1.0	36
13	Alternating matter motion in photoinduced mass transport driven and enhanced by light polarization in amorphous chalcogenide films. Applied Physics Letters, 2010, 97, 031905.	1.5	35
14	Structural-phase transformations in SiOx films in the course of vacuum heat treatment. Semiconductors, 2003, 37, 97-102.	0.2	28
15	Comparative studies of mechanical properties of stishovite and sapphire single crystals by nanoindentation. Journal of Superhard Materials, 2010, 32, 406-414.	0.5	26
16	Room Temperature Near-Infrared Photoresponse Based on Interband Transitions in \$hbox{In}_{0.35}hbox{Ga}_{0.65}hbox{As}\$ Multiple Quantum Dot Photodetector. IEEE Electron Device Letters, 2008, 29, 224-227.	2.2	25
17	Light-induced mass transport in amorphous chalcogenides: Toward surface plasmon-assisted nanolithography and near-field nanoimaging. Physica Status Solidi (B): Basic Research, 2014, 251, 1354-1362.	0.7	25
18	Preparation and optical properties of highly luminescent colloidal single-layer carbon nitride. RSC Advances, 2015, 5, 46843-46849.	1.7	24

#	Article	IF	CITATIONS
19	Electron beam-induced mass transport in As–Se thin films: compositional dependence and glass network topological effects. Journal Physics D: Applied Physics, 2013, 46, 245303.	1.3	21
20	Fabrication of Periodic Plasmonic Structures Using Interference Lithography and Chalcogenide Photoresist. Nanoscale Research Letters, 2015, 10, 497.	3.1	21
21	Au-TiB x -n-6H-SiC Schottky barrier diodes: Specific features of charge transport in rectifying and nonrectifying contacts. Semiconductors, 2009, 43, 865-871.	0.2	20
22	Structural transformation and functional properties of vanadium oxide films after low-temperature annealing. Thin Solid Films, 2014, 564, 179-185.	0.8	20
23	Field and photo-field electron emission from self-assembled Ge–Si nanostructures with quantum dots. Progress in Surface Science, 2003, 74, 305-318.	3.8	19
24	Gigantic uphill diffusion during self-assembled growth of Ge quantum dots on strained SiGe sublayers. Applied Physics Letters, 2010, 96, .	1.5	19
25	Luminescent ZnS:Cu films prepared by chemical methods. Semiconductors, 2000, 34, 1128-1132.	0.2	18
26	Influence of plasma discharge on the structure of polytetrafluoroethylene film and step coverage on polymer substrate. Materials Science and Engineering C, 2007, 27, 1227-1231.	3.8	17
27	Nanoscale Electrostructural Characterization of Compositionally Graded Al _{<i>x</i>} Ga _{1–<i>x</i>} N Heterostructures on GaN/Sapphire (0001) Substrate. ACS Applied Materials & Interfaces, 2015, 7, 23320-23327.	4.0	17
28	Selective light-induced mass transport in amorphous As x Se 100â^'x films driven by the composition tuning: Effect of temperature on maximum acceleration. Journal of Non-Crystalline Solids, 2018, 493, 86-93.	1.5	17
29	Deep traps in GaAs/InGaAs quantum wells and quantum dots, studied by noise spectroscopy. Journal of Applied Physics, 2008, 104, 103709.	1.1	16
30	E-beam induced mass transport in amorphous As20Se80 films. Materials Letters, 2012, 85, 113-116.	1.3	16
31	Direct Magnetic Relief Recording Using As40S60: Mn–Se Nanocomposite Multilayer Structures. Nanoscale Research Letters, 2017, 12, 286.	3.1	16
32	Polarization Effects in Graded AlGaN Nanolayers Revealed by Current-Sensing and Kelvin Probe Microscopy. ACS Applied Materials & Interfaces, 2018, 10, 6755-6763.	4.0	16
33	Persistence of (In,Ga)As quantum-dot chains under index deviation from GaAs(100). Applied Physics Letters, 2004, 84, 4681-4683.	1.5	15
34	Two-dimensional ordering of (In,Ga)As quantum dots in vertical multilayers grown on GaAs(100) and (n11). Applied Physics Letters, 2007, 91, .	1.5	15
35	Synthesis and properties of porous SiC ceramics. Journal of Applied Physics, 2010, 107, .	1.1	15
36	Nanomechanical properties of pure and doped Ta ₂ O ₅ and the effect of microwave irradiation. Journal Physics D: Applied Physics, 2012, 45, 475304.	1.3	15

#	Article	IF	CITATIONS
37	Theoretical and experimental investigations of single- and multilayer structures with SiGe nanoislands. Materials Science and Engineering C, 2003, 23, 1027-1031.	3.8	14
38	Interface roughness scattering in laterally coupled InGaAs quantum wires. Applied Physics Letters, 2010, 97, 262103.	1.5	14
39	Isotropic Hall effect and "freeze-in―of carriers in the InGaAs self-assembled quantum wires. Journal of Applied Physics, 2011, 110, .	1.1	14
40	Dynamic of Laser Ablation in SiC. Materials Science Forum, 2004, 457-460, 411-414.	0.3	13
41	Initial stages of chain formation in a single layer of (In,Ga)As quantum dots grown on GaAs (100). Applied Physics Letters, 2007, 91, .	1.5	13
42	One-dimensional features of In(Ga)As/GaAs dot chain structures with changeable interdot coupling. New Journal of Physics, 2009, 11, 043022.	1.2	13
43	Characterization of graphene layers by Kelvin probe force microscopy and microâ€Raman spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1172-1175.	0.8	13
44	Plasma treatment as a versatile tool for tuning of sorption properties of thin nanoporous carbon films. Applied Surface Science, 2021, 544, 148876.	3.1	13
45	Observation of unique blister-like surface features on amorphous metallic alloys following bombardment with deuterium ions. Journal of Nuclear Materials, 2008, 376, 125-127.	1.3	12
46	Influence of template type and buffer strain on structural properties of GaN multilayer quantum wells grown by PAMBE, an x-ray study. Journal Physics D: Applied Physics, 2011, 44, 025403.	1.3	12
47	The Peculiarities of Strain Relaxation in GaN/AlN Superlattices Grown on Vicinal GaN (0001) Substrate: Comparative XRD and AFM Study. Nanoscale Research Letters, 2016, 11, 252.	3.1	12
48	Photoluminescence, conductivity and structural study of terbium doped ZnO films grown on different substrates. Materials Science in Semiconductor Processing, 2019, 94, 51-56.	1.9	12
49	CdSe nanoparticles grown with different chelates. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2006, 9, 75-79.	0.3	12
50	Laser processing and characterization of ZnS–Cu thin films. Applied Surface Science, 2005, 247, 434-439.	3.1	11
51	Electron-beam induced variation of surface profile in amorphous As20Se80 films. Journal of Applied Physics, 2014, 115, .	1.1	11
52	Multifractal analysis of areas of spatial forms on surface of Zn Cd1â^'Te–Si (111) heterocompositions. Journal of Crystal Growth, 2014, 404, 204-209.	0.7	11
53	Local Strain and Crystalline Defects in GaN/AlGaN/GaN(0001) Heterostructures Induced by Compositionally Graded AlGaN Buried Layers. Crystal Growth and Design, 2019, 19, 200-210.	1.4	11
54	Microwave-stimulated relaxation of internal strains in GaAs-based device heterostructures. Technical Physics Letters, 2002, 28, 154-156.	0.2	10

#	Article	IF	CITATIONS
55	Effect of dimensionality and morphology on polarized photoluminescence in quantum dot-chain structures. Journal of Applied Physics, 2012, 112, .	1.1	10
56	Formation of Nanoporous Anodic Alumina by Anodization of Aluminum Films on Class Substrates. Nanoscale Research Letters, 2016, 11, 203.	3.1	10
57	Structure and Properties of WC–Co Composites with Different CrB2 Concentrations, Sintered by Vacuum Hot Pressing, for Drill Bits. Journal of Superhard Materials, 2021, 43, 344-354.	0.5	10
58	Diluted magnetic semiconductors based on II–VI, III–VI, and IV–VI compounds. Low Temperature Physics, 2009, 35, 62-70.	0.2	9
59	Tailoring the electrical properties of Ge/GaAs by film deposition rate and preparation of fully compensated Ge films. Physical Review B, 2011, 84, .	1.1	9
60	Effect of film growth rate and thickness on properties of Ge/GaAs(100) thin films. Thin Solid Films, 2014, 550, 715-722.	0.8	9
61	Optical and structural properties of Mn-doped ZnO nanorods grown by aqueous chemical growth for spintronic applications. Thin Solid Films, 2016, 601, 22-27.	0.8	9
62	Investigation of undoped and Tb-doped ZnO films on Al2O3 substrate by infrared reflection method. Thin Solid Films, 2019, 673, 136-140.	0.8	9
63	Magnetic and optical properties of printed ZnO:Co polycrystalline layers. Materials Science in Semiconductor Processing, 2021, 135, 106054.	1.9	9
64	The influence of TiB2-thin film thickness on metal–GaAs structural characteristics. Thin Solid Films, 2000, 373, 79-83.	0.8	8
65	Near/Far-Field Investigations of the Interaction between Surface Waves and Nanoparticles. Physica Status Solidi (B): Basic Research, 2002, 229, 1283-1294.	0.7	8
66	Effect of microwave annealing on silicon dioxide/silicon carbide structures. Technical Physics, 2003, 48, 598-601.	0.2	8
67	Multifractal spectrums for volumes of spatial forms on surface of Zn x Cd 1â^'x Te–Si (111) heterostructures and estimation of the fractal surface energy. Journal of Crystal Growth, 2016, 450, 28-33.	0.7	8
68	Au Gratings Fabricated by Interference Lithography for Experimental Study of Localized and Propagating Surface Plasmons. Nanoscale Research Letters, 2017, 12, 190.	3.1	8
69	Impact of Surface Plasmon Polaritons on Silver Photodiffusion into As2S3 Film. Plasmonics, 2021, 16, 181-188.	1.8	8
70	AFM surface imaging of thermally oxidized hydrogenated crystalline silicon. Applied Surface Science, 2002, 191, 148-152.	3.1	7
71	Giant enhancement of elastic surface plasmon-polariton scattering. Optics Express, 2010, 18, 43.	1.7	7
72	Structural study of Ge/GaAs thin films. Journal of Physics: Conference Series, 2012, 371, 012040.	0.3	7

#	Article	IF	CITATIONS
73	Improved core model of indentation and its application to measure diamond hardness. Journal of Superhard Materials, 2016, 38, 289-305.	0.5	7
74	Direct Determination of 3D Distribution of Elemental Composition in Single Semiconductor Nanoislands by Scanning Auger Microscopy. Nanoscale Research Letters, 2016, 11, 103.	3.1	7
75	Kinetically controlled transition from 2D nanostructured films to 3D multifaceted InN nanocrystals on GaN(0001). CrystEngComm, 2018, 20, 1499-1508.	1.3	7
76	Interphase interactions and features of structural relaxation in TiBx-n-GaAs (InP, GaP, 6H-SiC) contacts subjected to active treatment. Semiconductors, 2004, 38, 737-741.	0.2	6
77	Conductive-atomic force microscopy characterization of Ta ₂ O ₅ /SiO ₂ stacks and the effect of microwave irradiation. Journal Physics D: Applied Physics, 2009, 42, 145301.	1.3	6
78	Conducting and topographic AFM analysis of Hf-doped and Al-doped Ta2O5 films. Thin Solid Films, 2011, 519, 8182-8190.	0.8	6
79	Scanning confocal Raman spectroscopy of silicon phase distribution in individual Si nanowires. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1012-1016.	0.8	6
80	Structure and mechanical properties of Ti-Al-Si-N protective coatings deposited from separated plasma of a vacuum arc. Journal of Superhard Materials, 2013, 35, 20-28.	0.5	6
81	Substrate-induced self-assembly of donor–acceptor type compounds with terminal thiocarbonyl groups. Thin Solid Films, 2013, 539, 127-133.	0.8	6
82	Formation of Nanoscale Structures on Chalcogenide Films. Physica Status Solidi (B): Basic Research, 2018, 255, 1700405.	0.7	6
83	Structure and Mechanical Properties of Ti–Al–C and Ti–Al–Si–C Films: Experimental and First-Principles Studies. Journal of Superhard Materials, 2021, 43, 100-110.	0.5	6
84	Growth-sector dependence of morphological, structural and optical features in boron-doped HPHT diamond crystals. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2021, 24, 261-271.	0.3	6
85	Impact of defects on photoexcited carrier relaxation dynamics in GeSn thin films. Journal of Physics Condensed Matter, 2020, 33, 065702.	0.7	6
86	Ultrasonic assisted nanomanipulations with atomic force microscope. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2009, 13, 036-042.	0.3	6
87	Reflectometry Study of Nanoporous Films with Arrays of Gold Nanoparticles. Ukrainian Journal of Physics, 2014, 59, 915-921.	0.1	6
88	Chemically produced ZnS: Cu films: Structure, properties, and mechanism of electroluminescence. Technical Physics, 2002, 47, 978-982.	0.2	5
89	Microsize defects in InGaAs/GaAs A/B multilayers quantum dot stacks. Journal of Crystal Growth, 2005, 284, 47-56.	0.7	5

90 Changes of Surface Properties of Yeast Cell Wall Under Exposure of Electromagnetic Field (40.68) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50

#	Article	IF	CITATIONS
91	Lateral ordering of quantum dots and wires in the (In,Ga)As/GaAs(100) multilayer structures. Semiconductors, 2007, 41, 73-80.	0.2	5
92	Engineering of 3D self-directed quantum dot ordering in multilayer InGaAs/GaAs nanostructures by means of flux gas composition. Nanotechnology, 2008, 19, 505605.	1.3	5
93	Threeâ€dimensional ordering in selfâ€organized (In,Ga)As quantum dot multilayer structures. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1748-1751.	0.8	5
94	Multifractal parameterization of space forms on surfaces of Zn x Cd1 â^' x Te-Si(111) heterocompositions and its relationship to the conditions of layer synthesis. Russian Journal of Physical Chemistry A, 2014, 88, 1375-1381.	0.1	5
95	Effect of well/barrier thickness ratio on strain relaxation in GaN/AlN superlattices grown on GaN/sapphire template. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	5
96	Strain relaxation in GaN/AlN superlattices on GaN(0001) substrate: Combined superlattice-to-substrate lattice misfit and thickness-dependent effects. Materials and Design, 2018, 157, 141-150.	3.3	5
97	Highly porous carbon films fabricated by magnetron plasma enhanced chemical vapor deposition: Structure, properties and implementation. Applied Surface Science, 2019, 496, 143735.	3.1	5
98	Toward deposition of organic solid with controlled morphology on selected surfaces. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	5
99	Plasmon-Stimulated Photodoping in the Thin-Layer As2S3–Ag Structure. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2019, 127, 938-942.	0.2	5
100	Growth kinetics and nanoscale structure-property relationships of InN nanostructures on GaN(0Â0Â0Â1). Applied Surface Science, 2021, 537, 147997.	3.1	5
101	Indium segregation in ultra-thin In(Ga)As/GaAs single quantum wells revealed by photoluminescence spectroscopy. Applied Physics Letters, 2021, 118, .	1.5	5
102	Effect of electron-beam treatment of sensor glass substrates for SPR devices on their metrological characteristics. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 444-451.	0.3	5
103	Digital micro-photogrammetry in analysis and modeling habit and sectoral structure of real high-pressure high-temperature single-crystal diamonds. Review of Scientific Instruments, 2022, 93, 033903.	0.6	5
104	Self formation of Si nanostructured layer at the metal silicide/silicon interface. Materials Science and Engineering C, 2003, 23, 181-186.	3.8	4
105	Formation of nanostructure on surface of SiC by laser radiation. Physica Status Solidi A, 2003, 195, 199-203.	1.7	4
106	Peculiarities of the formation and thermal stability of barrier contacts in high-sensitivity silicon carbide detector diodes. Technical Physics Letters, 2003, 29, 22-25.	0.2	4
107	Phase Transition on Surface of IV Group Semiconductors by Laser Radiation. Solid State Phenomena, 2005, 108-109, 345-350.	0.3	4
108	Direct surface relief formation in As-S(Se) layers. Proceedings of SPIE, 2010, , .	0.8	4

#	Article	IF	CITATIONS
109	Effects of the lateral ordering of self-assembled SiGe nanoislands grown on strained Si1 â^' x Ge x buffer layers. Semiconductors, 2012, 46, 647-654.	0.2	4
110	Magnetic and structural changes in the near-surface epitaxial Y ₂₉₅ La ₀₀₅ Fe ₅ O ₁₂ films after high-dose ion implantation. Applied Optics, 2016, 55, B144.	0.9	4
111	RF plasma treatment of shallow ion-implanted layers of germanium. Materials Science in Semiconductor Processing, 2016, 42, 204-209.	1.9	4
112	Surface potential of meso-dimensional ZnS:Mn particles obtained using SHS method. Journal of Nanoparticle Research, 2018, 20, 1.	0.8	4
113	Efficient SERS substrates based on laterally ordered gold nanostructures made using interference lithography. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 215-223.	0.3	4
114	A silicon carbide thermistor. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2006, 9, 67-70.	0.3	4
115	Formation of nanostructures on surface of SiC by laser radiation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 155-158.	1.7	3
116	Phase and structural changes stimulated in multilayer contacts to n-GaAs by rapid thermal annealing. Semiconductors, 2003, 37, 1114-1118.	0.2	3
117	Barrier Material Improvement in AlGaN/GaN Microwave Transistors Under Gamma Irradiation Treatment. Materials Research Society Symposia Proceedings, 2003, 764, 1.	0.1	3
118	Spectral Characteristics and Surface Morphology of Organic Polymer Films Containing Vanadium Pentoxide Nanoparticles. Russian Journal of Electrochemistry, 2004, 40, 259-266.	0.3	3
119	Self-Organization of Three-Dimensional Lead Telluride Nanoislands under Conditions Close to Thermodynamic Equilibrium. Technical Physics Letters, 2005, 31, 716.	0.2	3
120	Quantized field-electron emission at 300K in self-assembled arrays of silicon nanowires. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 37, 212-217.	1.3	3
121	Alignment and optical polarization of InGaAs quantum wires on GaAs high index surfaces. Materials Letters, 2011, 65, 1427-1430.	1.3	3
122	Identification of nanoscale structure and morphology reconstruction in oxidized a-SiC:H thin films. Applied Surface Science, 2012, 260, 73-76.	3.1	3
123	Calcein and calceinâ^'Ag films under vapor exposure: Sensing properties and reversible film restructuring. Talanta, 2012, 101, 267-272.	2.9	3
124	Temperature driven three-dimensional ordering of InGaAs/GaAs quantum dot superlattices grown under As2 gas flux. Applied Surface Science, 2014, 305, 689-696.	3.1	3
125	Spatial distribution of free carrier concentration in vertical GaN Gunnâ€diode structures studied by confocal microâ€Raman spectroscopy and Kelvin probe force microscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 269-273.	0.8	3
126	Mechanisms of the degradation of Schottky-barrier photodiodes based on ZnS single crystals. Semiconductors, 2016, 50, 112-119.	0.2	3

#	Article	IF	CITATIONS
127	Invariance of multifractal spectrums of spatial forms on the surface of ZnxCd1-xTe – Si heterocompositions synthesized by electron beam epitaxy and hot wall epitaxy. Journal of Crystal Growth, 2017, 475, 144-149.	0.7	3
128	Enhanced recrystallization and dopant activation of P+ ion-implanted super-thin Ge layers by RF hydrogen plasma treatment. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	3
129	Micro-Raman spectroscopy and electrical conductivity of graphene layer on SiO ₂ dielectric subjected to electron beam irradiation. Materials Research Express, 2018, 5, 116405.	0.8	3
130	Investigation of structural changes in AsxSe100-x amorphous thin films after electron beam irradiation with XAFS, XANES and Kelvin force microscopy. Applied Surface Science, 2020, 530, 147266.	3.1	3
131	Influence of different aligning surfaces on the morphology of dichroic squaraine films. Polymer Bulletin, 2021, 78, 1313-1329.	1.7	3
132	Nanoprobe spectroscopy of capillary forces and its application for a real surface diagnostics. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2010, 13, 111-124.	0.3	3
133	Laser oscillation in Cr2+ :ZnS waveguide thin-film structures under electrical pumping with impact excitation mechanism. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2011, 14, 339-343.	0.3	3
134	Growth of silicon self-assembled nanowires by using gold-enhanced CVD technology. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2018, 21, 282-287.	0.3	3
135	Structural, optical and magnetic properties of stencil-free printed ZnO layers doped with Fe2+ and Fe3+ ions. Materials Chemistry and Physics, 2022, 276, 125329.	2.0	3
136	Current transfer processes in a hydrated layer localized in a two-layer porous structure of nanosized ZrO2. Journal of Materials Science: Materials in Electronics, 2022, 33, 2753-2764.	1.1	3
137	On the nature of transition layer and heat tolerance of TiBx/GaAs-based contacts. Applied Surface Science, 2000, 166, 520-525.	3.1	2
138	Electrolytic Preparation of Vanadium(V) Oxide from Saturated Solutions of Ammonium Metavanadate. Russian Journal of Applied Chemistry, 2001, 74, 1474-1478.	0.1	2
139	Effect of Rapid Thermal Annealing Conditions on Parameters of Ni/21R-SiC Contacts. Materials Science Forum, 2002, 389-393, 905-908.	0.3	2
140	Electrolytic Synthesis of Binary Oxide Systems Based on Manganese(II) Oxide. Russian Journal of Applied Chemistry, 2002, 75, 213-218.	0.1	2
141	Nanocomposite Si/Diamond Layers: Room Temperature Visible-Light Emitting Systems. Chemical Vapor Deposition, 2003, 9, 139-143.	1.4	2
142	Electrolytic Iron Sulfide Products in Lithium Batteries. Russian Journal of Electrochemistry, 2004, 40, 736-742.	0.3	2
143	Formation of rocking curves for quasi-forbidden reflections in short-periodic superlattices GaAs/AlGaAs. Journal of Applied Crystallography, 2004, 37, 150-155.	1.9	2
144	Thermal stability of multilayer contacts on gallium nitride. Technical Physics Letters, 2005, 31, 1078-1081.	0.2	2

#	Article	IF	CITATIONS
145	Radiation effects and interphase interactions in ohmic and barrier contacts to indium phosphide as induced by rapid thermal annealing and irradiation with γ-ray 60Co photons. Semiconductors, 2010, 44, 1559-1566.	0.2	2
146	Macro- and nanoscopic capillary effects on nanostructured real surfaces. Journal of Superhard Materials, 2012, 34, 81-94.	0.5	2
147	Effect of electron beam irradiation on structural and electrical properties of graphene-SiO <inf>2</inf> -Si structures. , 2017, , .		2
148	Sputtering effects on mirrors made of different tungsten grades. Journal of Nuclear Materials, 2018, 500, 56-63.	1.3	2
149	Modification of GaN thin film on sapphire substrate optical properties under weak magnetic fields. Materials Research Express, 2019, 6, 036413.	0.8	2
150	Graphitic Nanoporous Carbon Thin Films: Fabrication Method, Structural, Electrical and Gas Sensor Properties. ECS Transactions, 2020, 97, 151-156.	0.3	2
151	Conductivity-Type Conversion in Self-Assembled GeSn Stripes on Ge/Si(100) under Electric Field. ACS Applied Electronic Materials, 2021, 3, 4388-4397.	2.0	2
152	Graphene layers fabricated from the Ni/a-SiC bilayer precursor. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 322-330.	0.3	2
153	Light-induced mass transport in amorphous chalcogenides/gold nanoparticles composites. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 354-361.	0.3	2
154	The growth of weakly coupled graphene sheets from silicon carbide powder. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2014, 17, 301-307.	0.3	2
155	Screen-printed p-CdTe layers for CdS/CdTe solar cells. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2008, 8, 61-65.	0.3	2
156	Magnetic force microscopy of YLaFeO films implanted by high dose of nitrogen ions. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2013, 16, 246-252.	0.3	2
157	Estimation of the Relative Energy of Grain Boundaries in Silicon Films by the Grain Boundary Grooves Method. Journal of Nano- and Electronic Physics, 2018, 10, 06040-1-06040-4.	0.2	2
158	Magnetic Microstructure of Epitaxial Films of LaGa-Substituted Yttrium Iron Garnet. Metallofizika I Noveishie Tekhnologii, 2019, 41, 529-548.	0.2	2
159	Joint Electrolytic Deposition of Vanadium and Manganese Oxides. Russian Journal of Applied Chemistry, 2002, 75, 552-557.	0.1	1
160	Electrolytic Deposition of Cobalt(III) Oxide in the Presence of Nickel(II) and Chromium(III) Ions. Russian Journal of Applied Chemistry, 2002, 75, 905-910.	0.1	1
161	Special features of formation and characteristics of Ni/21R-SiC Schottky diodes. Semiconductors, 2003, 37, 456-461.	0.2	1
162	Fabrication and cathodoluminescent properties of the ZnO-Cu,Ga and ZnS-Cu,Ga film phosphors. Journal of the Society for Information Display, 2003, 11, 21.	0.8	1

#	Article	IF	CITATIONS
163	Laser Assisted Formation of SiC Nano-Tips for Field Emission Application. Solid State Phenomena, 2003, 94, 145-150.	0.3	1
164	Composition and elastic stresses in multilayer structures with Silâ^'x Gex nanoislands. Physics of the Solid State, 2004, 46, 85-88.	0.2	1
165	Effect of surface energy minima on the shape of self-induced SiGe nanoislands. Physica Status Solidi (B): Basic Research, 2005, 242, 2833-2837.	0.7	1
166	Properties of barrier contacts with nanosize TiB x layers to InP. Semiconductors, 2008, 42, 777-782.	0.2	1
167	On the complex behavior of strain relaxation in (In,Ga)As/GaAs(001) quantum dot molecules. Applied Physics Letters, 2009, 95, 023103.	1.5	1
168	Precise Manipulations with Asymmetric Nano-Objects Viscoelastically Bound to a Surface. Journal of Nano Research, 2016, 39, 256-276.	0.8	1
169	Transformation of graphene flakes into carbon nanostructures byl ³ -irradiation. Materials Research Express, 2017, 4, 045602.	0.8	1
170	Formation of Nanostructures Upon Photoexcitation of Surface Plasmon Resonance in Nanocomposites Derived from Textured Gold Films and Chalcogenide Glass. Theoretical and Experimental Chemistry, 2018, 54, 107-113.	0.2	1
171	Variations of morphology of fluoropolymer thin films versus deposition conditions. Surface Topography: Metrology and Properties, 2021, 9, 045006.	0.9	1
172	Scanning Probe Microscopy in Practical Diagnostic: 3D Topography Imaging and Nanometrology. Engineering Materials, 2014, , 179-219.	0.3	1
173	Morphology of sulphur-terminated compound deposits condensed on different substrates in vacuum. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2015, 18, 433-437.	0.3	1
174	Mechanical scanning probe nanolithography: modeling and application. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2012, 15, 321-327.	0.3	1
175	Microanalysis of magnetic structure of yttrium-iron garnet films by using the scanning probe microscopy methods. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2016, 19, 90-97.	0.3	1
176	The influence of substrate temperature on properties of Cu-Al-O films deposited using the reactive ion beam sputtering method. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2017, 20, 314-318.	0.3	1
177	Phase Formation and Physicomechanical Properties of WC–Co–CrB2 Composites Sintered by Vacuum Hot Pressing for Drill Tools. Journal of Superhard Materials, 2022, 44, 1-11.	0.5	1
178	Using Digital Microphotogrammetry for Morphology Analysis of HPHT-Diamond Single Crystals. Journal of Superhard Materials, 2021, 43, 457-459.	0.5	1
179	<title>Liquid phase epitaxial III-V technology for photodetectors manufacturing</title> . , 1997, 3182, 146.		0
180	Photoluminescence investigation of Dy incorporation into InP during liquid phase epitaxy. , 1998, 3359, 197.		0

#	Article	IF	CITATIONS
181	Relaxation processes in Au–TiB2/GaAs structures under short-term thermal annealing. Applied Surface Science, 2000, 166, 130-136.	3.1	Ο
182	Heat-resistant Au-ZrB/sub x/-n-SiC 6H Schottky barriers. , 0, , .		0
183	<title>Complex nanostructured silicon wire</title> ., 2002, 4806, 323.		0
184	Influence of rapid thermal annealing modes on the parameters of Ni/21R-SiC contacts. , 0, , .		0
185	Interactions between phases and thermal stability of TiB/sub x/(ZrB/sub x/)-n-SiC 6H contacts. , 0, , .		Ο
186	Nanostructure Formation on a Surface of 6H-SiC by Laser Radiation. Materials Science Forum, 2003, 433-436, 595-598.	0.3	0
187	<title>Nanostructures formation on surface of 6H-SiC by
N<formula><inf><roman>2</roman></inf></formula> laser radiation</title> . , 2003, , .		0
188	Nanostructures for formation on surface of 6H-SiC by laser radiation. , 2003, , .		0
189	Correlation between the energy of SiGe nanoislands and their shape and size. Physics of the Solid State, 2004, 46, 67-70.	0.2	0
190	Oxidation of hydrogenated crystalline silicon as an alternative approach for ultrathin SiO2growth. Journal of Physics: Conference Series, 2005, 10, 246-250.	0.3	0
191	<title>Formation of nanohills on the surface of 6<emph type="1">H</emph>-SiC:N at an early stage of
laser ablation</title> . , 2005, , .		0
192	The correlation between the surface-energy minima and the shape of self-induced SiGe nanoislands. Semiconductors, 2006, 40, 385-390.	0.2	0
193	Multi-color Photoresponse Based on Interband and Intersubband Transitions in InAs and InGaAs Quantum Dot Photodetectors. Materials Research Society Symposia Proceedings, 2007, 1055, 2.	0.1	0
194	Broadband photoresponse from InAs quantum dots embedded in a graded well for visible to mid-infrared detection. Proceedings of SPIE, 2008, , .	0.8	0
195	Bright emission from amorphous sicn thin films. , 2010, , .		0
196	Carbon-rich nanostructured a-SiC for cold emitters. , 2013, , .		0
197	Ge/GaAs thin films for thermometer and bolometer application. , 2013, , .		0
198	Carbon-Rich Nanostructurated a-SiC on Si Heterostructures for Field-Effect Electron Emission. Advanced Materials Research, 0, 854, 59-67.	0.3	0

0

#	Article	IF	CITATIONS
199	Nano- and micro-scale morghological defects in oxidized a-SiC:H thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 619-623.	0.8	0
200	Ordering of InGaAs Quantum Dots Grown by Molecular Beam Epitaxy under As2 gas flux. Materials Research Society Symposia Proceedings, 2015, 1792, 1.	0.1	0
201	Hydrogen plasma modification of shallow implanted Germanium layers. , 2016, , .		0
202	ELECTRONIC AND STRUCTURAL PROPERTIES OF Si–Gd–O ELECTRON EMITTER. Surface Review and Letters, 2020, 27, 1950089.	0.5	0
203	Impact of low energy ion beams on the properties of rr-P3HT films. Applied Surface Science, 2021, 535, 147619.	3.1	0
204	Peculiarities Of Th.Terrestris Spores Surface Ultrastructure Investigated By Afm. , 2002, , 341-346.		0
205	Title is missing!. Ukrainian Journal of Physical Optics, 2005, 6, 78-86.	9.7	0
206	Fabrication, properties and application of Ge-on-GaAs thin nanoheterogeneous films. Tekhnologiya I Konstruirovanie V Elektronnoi Apparature, 2014, , 39-44.	0.1	0
207	Platinum Nanoparticles with Adsorptive Layer of Chlorella vulgaris Polysaccharides Inactivate Tumor Cells of Ascitic Ehrlich Carcinoma, Ovarian Cancer and Leukemia. Springer Proceedings in Physics, 2015, , 257-268.	0.1	0
208	Development of Technology for Sensor Chip Production with Increased Sensitivity and Improved Physical and Mechanical Characteristics for Optical Sensors Based on Surface Plasmon Resonance. Science and Innovation, 2017, 13, 25-33.	0.2	0
209	Features of mechanical scanning probe lithography on graphene oxide and As(Ge)Se chalcogenide resist. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2018, 21, 152-159.	0.3	0
210	Control of plasmons excitation by P- and S-polarized light in gold nanowire gratings by azimuthal angle variation. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 353-360.	0.3	0
211	Mechanical strain in the structure of array of silicon nanowires grown on a silicon substrate. Semiconductor Physics, Quantum Electronics and Optoelectronics, 2019, 22, 293-298.	0.3	0
212	Shear-Induced Metallization on the (001) and (111) Faces of Diamond during Hardness Tests. Journal of Superhard Materials, 2021, 43, 379-391.	0.5	0
213	ĐаĐįÑ–Đ²ĐįÑ€Đ¾Đ²Ñ–ĐƊ½Đ,ĐºĐ¾Đ²Ñ– HPHT-Đ°Đ»Đ¼Đ°Đ-Đ, ÑĐº ааÑ,Đ,Đ2Đ½Ñ– ĐµĐ»ĐµĐ¼ĐµĐ½	ĩÑ¢ĐộеĐ	»ĐµĐ⁰Ñ,Ñ€

²¹⁴ Defect engineering using microwave processing in SiC and GaAs. Semiconductor Science and 1.0